

Abstracts

A Novel GaAs FET Oscillator with Low Phase Noise

A.N. Riddle and R.J. Trew. "A Novel GaAs FET Oscillator with Low Phase Noise." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 257-260.

A novel GaAs FET oscillator circuit is presented. This circuit is capable of reducing phase noise up to 20 db. A source-coupled pair of GaAs FETs has a balanced characteristic which can eliminate both the reactive and resistive modulation mechanisms which upconvert I/f noise. This circuit is inherently broadband and ideal for monolithic implementations.

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